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Publisher	AIP Publishing LLC
Publication	Journal of Vacuum Science & Technology B
Article Title	Structural, morphological, and defect properties of metamorphic In <sub>0.7</sub> Ga <sub>0.3</sub> As/GaAs <sub>0.35</sub> Sb <sub>0.65</sub> p-type tunnel field effect transistor structure grown by molecular beam epitaxy
Author	Yan Zhu, Mantu K. Hudait, Dheeraj K. Mohata, et al.
Online Publication Date	Jul 3, 2013
Volume number	31
Issue number	4
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Requestor type	Author (original article)
Format	Electronic
Portion	Figure/Table
Number of figures/tables	8
Title of your thesis / dissertation	Mixed As/Sb and tensile strained Ge/InGaAs heterostructures for low-power tunnel field effect transistors
Expected completion date	Apr 2014
Estimated size (number of pages)	240
Total	0.00 USD

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Publisher	AIP Publishing LLC
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Article Title	Structural properties and band offset determination of p-channel mixed As/Sb type-II staggered gap tunnel field-effect transistor structure
Author	Y. Zhu,N. Jain,D. K. Mohata, et al.
Online Publication Date	Sep 12, 2012
Volume number	101
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Format	Electronic
Portion	Figure/Table
Number of figures/tables	8
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Expected completion date	Apr 2014
Estimated size (number of pages)	240
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**Title:** Reliability Studies on High-Temperature Operation of Mixed As/Sb Staggered Gap Tunnel FET Material and Devices

**Author:** Yan Zhu; Mohata, D.K.; Datta, S.; Hudait, M.K.

**Publication:** Device and Materials Reliability, IEEE Transactions on

**Publisher:** IEEE

**Date:** March 2014

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**Title:** Tensile-Strained Nanoscale Ge/In<sub>0.16</sub>Ga<sub>0.84</sub>As Heterostructure for Tunnel Field-Effect Transistor

**Author:** Yan Zhu, Deepam Maurya, Shashank Priya, and Mantu K. Hudait

**Publication:** Applied Materials

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